

PRELIMINARY TECHNICAL DATA

a

Precision Very Low Noise Low Input Bias Current Wide Bandwidth JFET Operational Amplifiers

Preliminary Technical Data

AD8610

FEATURES

Low noise: $6\text{nV}/\sqrt{\text{Hz}}$
Low Offset Voltage: $100\mu\text{V}$ max.
Low input Bias current 10pA max.
Fast settling: 600ns to 0.01%
Low Distortion
Unity Gain Stable
No Phase Reversal
Dual supply operation: $\pm 5\text{V}$ to $\pm 13\text{V}$

APPLICATIONS

Photodiode Amplifier
ATE
Instrumentation
Sensors and Controls
Precision filters
High Fidelity Audio

GENERAL DESCRIPTION

The AD8610 is a precision JFET input amplifier featuring very low offset voltage and drift, very low input voltage and current noise, very low input bias current and wide bandwidth. Outputs are stable with capacitive loads of over 500pF in non-inverting unity gain. Output swings to within 1.2V of the supplies even with a 1kohm load, maximizing dynamic range with limited supply voltages.

Applications for these amplifiers include electronic instruments, ATE front-end amplification and integrator circuits, CAT/MRI/Ultrasound medical instrumentation, photodiode amplification, fast precision filters and professional quality audio.

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AD8610

ELECTRICAL CHARACTERISTICS (@ $V_S = \pm 5.0V$, $V_{CM} = 0V$, $T_A = +25^\circ C$ unless noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
INPUT CHARACTERISTICS						
Offset Voltage AD8610B	V_{OS}	$-40^\circ C < T_A < +125^\circ C$			100	μV
Offset Voltage AD8610A	V_{OS}	$-40^\circ C < T_A < +125^\circ C$			200	μV
		$+25^\circ C < T_A < +125^\circ C$			250	μV
		$-40^\circ C < T_A < +125^\circ C$			350	μV
Input Bias Current	I_B	$-40^\circ C < T_A < +125^\circ C$	-10		10	pA
		$-40^\circ C < T_A < +85^\circ C$	-250		250	pA
		$-40^\circ C < T_A < +125^\circ C$	-2.5		2.5	nA
Input Offset Current	I_{OS}	$-40^\circ C < T_A < +85^\circ C$	-10		10	pA
		$-40^\circ C < T_A < +125^\circ C$	-75		75	pA
		$-40^\circ C < T_A < +125^\circ C$	-150		150	pA
Input Voltage Range			-2		3	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -1.5V$ to $2.5V$	90	95		dB
Large Signal Voltage Gain	A_{VO}	$R_L = 1 k\Omega$, $V_O = -3V$ to $3V$	100	200		V/mV
Offset Voltage Drift AD8610B	$\Delta V_{OS}/\Delta T$	$-40^\circ C < T_A < +125^\circ C$		0.3	1	$\mu V/^\circ C$
Offset Voltage Drift AD8610A	$\Delta V_{OS}/\Delta T$	$-40^\circ C < T_A < +125^\circ C$		0.3	3.5	$\mu V/^\circ C$
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$R_L = 1 k\Omega$, $-40^\circ C < T_A < +125^\circ C$	3.8			V
Output Voltage Low	V_{OL}	$R_L = 1 k\Omega$, $-40^\circ C < T_A < +125^\circ C$			-3.8	V
Output Current	I_{OUT}	$V_{Dropout} < 1.2V$		± 15		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = \pm 5 V$ to $\pm 13 V$	100	110		dB
Supply Current/Amplifier	I_{SY}	$V_O = 0V$ $-40^\circ C < T_A < +125^\circ C$			3000	μA
					3500	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2 k\Omega$	40	50		V/ μs
Gain Bandwidth Product	GBP			25		MHz
Settling time	t_s	$A_V = +1$, 4V step, to 0.01%		350		ns
NOISE PERFORMANCE						
Voltage Noise	e_n p-p	0.1 Hz to 10 Hz		1.2		μV p-p
Voltage Noise Density	e_n	$f = 1 kHz$		6		nV/ \sqrt{Hz}
Current Noise Density	i_n	$f = 1 kHz$		5		fA/ \sqrt{Hz}

PRELIMINARY TECHNICAL DATA

AD8610

ELECTRICAL CHARACTERISTICS (@ $V_S = \pm 13V$, $V_{CM} = 0V$, $T_A = +25^\circ C$ unless noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
INPUT CHARACTERISTICS						
Offset Voltage AD8610B	V_{OS}	$-40^\circ C < T_A < +125^\circ C$			100	μV
					200	μV
Offset Voltage AD8610A	V_{OS}	$+25^\circ C < T_A < +125^\circ C$			250	μV
		$-40^\circ C < T_A < +125^\circ C$			350	μV
					850	μV
Input Bias Current	I_B		-10		10	pA
	I_B	$-40^\circ C < T_A < +85^\circ C$	-250		250	pA
	I_B	$-40^\circ C < T_A < +125^\circ C$	-2.5		2.5	nA
Input Offset Current	I_{OS}		-10		10	pA
	I_{OS}	$-40^\circ C < T_A < +85^\circ C$	-75		75	pA
	I_{OS}	$-40^\circ C < T_A < +125^\circ C$	-150		150	pA
Input Voltage Range			-10.5		10.5	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -10V$ to $10V$	90	110		dB
Large Signal Voltage Gain	A_{VO}	$R_L = 1 k\Omega$, $V_o = -10V$ to $10V$	100	200		V/mV
Offset Voltage Drift AD8610B	$\Delta V_{OS}/\Delta T$	$-40^\circ C < T_A < +125^\circ C$		0.5	1	$\mu V/^\circ C$
Offset Voltage Drift AD8610A	$\Delta V_{OS}/\Delta T$	$-40^\circ C < T_A < +125^\circ C$		0.5	3.5	$\mu V/^\circ C$
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$R_L = 1 k\Omega$, $-40^\circ C < T_A < +125^\circ C$	-11.75			V
Output Voltage Low	V_{OL}	$R_L = 1 k\Omega$, $-40^\circ C < T_A < +125^\circ C$			11.75	V
Output Current	I_{OUT}			± 15		mA
Short Circuit Current	I_{SC}			± 65		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = \pm 5V$ to $\pm 13V$	100	110		dB
Supply Current/Amplifier	I_{SY}	$V_O = 0V$ $-40^\circ C < T_A < +125^\circ C$			3000	μA
					4000	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2 k\Omega$	40	60		V/ μs
Gain Bandwidth Product	GBP			25		MHz
Settling time	t_s	$A_v = +1$, 10V step, to 0.01%		600		ns
NOISE PERFORMANCE						
Voltage Noise	e_n p-p	0.1 Hz to 10 Hz		1.2		μV p-p
Voltage Noise Density	e_n	$f = 1 kHz$		6		nV/ \sqrt{Hz}
Current Noise Density	i_n	$f = 1 kHz$		5		fA/ \sqrt{Hz}

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ABSOLUTE MAXIMUM RATINGS¹

Supply voltage	27.3V
Input Voltage.....	Vs- to Vs+
Differential Input Voltage	±Supply Voltage
Output Short-Circuit Duration	Indefinite
Storage Temperature Range	
R, RM Package.....	-65°C to +150°C
Operating Temperature Range	
AD8610.....	-40°C to +85°C
Junction Temperature Range	
R, RM Package.....	-65°C to +150°C
Lead Temperature Range (Soldering, 60 Sec).....	+300°C

Package Type	θ_{JA}	θ_{JC}	Units
8-Pin MSOP (RM)	190	44	°C/W
8-Pin SOIC (R)	158	43	°C/W

NOTES

¹ Absolute maximum ratings apply at 25°C, unless otherwise noted.

² θ_{JA} is specified for the worst case conditions, i.e., θ_{JA} is specified for device soldered in circuit board for surface mount packages.

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
AD8610ARM	-40°C to +125°C	8-Pin MSOP	RM-8
AD8610AR	-40°C to +125°C	8-Pin SOIC	R-8
AD8610BR	-40°C to +125°C	8-Pin SOIC	R-8



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